Title (en)

ETCHING OF HIGH ASPECT RATIO FEATURES IN A SUBSTRATE

Title (de)

VERFAHREN ZUR ÄTUNG STRUKTUREN MIT HOHEM ASPEKTVERHÄLTNIS IN EINEM SUBSTRAT

Title (fr)

ATTAQUE DE CARACTERISTIQUES A RAPPORT DE FORME ELEVE DANS UN SUBSTRAT

Publication

EP 1330839 A2 20030730 (EN)

Application

EP 01987258 A 20011101

Priority

- US 0146210 W 20011101
- US 70488700 A 20001101
- US 70525400 A 20001101

Abstract (en)

[origin: WO0243116A2] A substrate processing chamber (110) comprisea a gas supply (56) to provide a gas to the chamber, first and second electrodes (115, 105) that may be electrically biased to energize the gas, the second electrode (115) being adapted to be chargeable to a power density of at least about 10 watts/cm<2>, and the second electrode (115) comprising a receiving surface (147) to receive a substrate (10), and an exhaust (110) to exhaust the gas.

IPC 1-7

H01L 21/3065; H01J 37/32

IPC 8 full level

H01L 21/3065 (2006.01); **H01J 37/32** (2006.01); **H01L 21/311** (2006.01)

IPC 8 main group level

H01L (2006.01)

CPC (source: EP KR)

H01J 37/32082 (2013.01 - EP); **H01J 37/3266** (2013.01 - EP); **H01L 21/306** (2013.01 - KR); **H01L 21/31116** (2013.01 - EP); H01J 2237/3347 (2013.01 - EP)

Citation (search report)

See references of WO 0243116A2

Designated contracting state (EPC)

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US 0146210 W 20011101; CN 01817958 A 20011101; EP 01987258 A 20011101; JP 2002544762 A 20011101; KR 20037006046 A 20030430